

54F/74F174 Hex D Flip-Flop with Master Reset

General Description

The 'F174 is a high-speed hex D flip-flop. The device is used primarily as a 6-bit edge-triggered storage register. The information on the D inputs is transferred to storage during the LOW-to-HIGH clock transition. The device has a Master Reset to simultaneously clear all flip-flops.

Features

- Edge-triggered D-type inputs
- Buffered positive edge-triggered clock
- Asynchronous common reset
- Guaranteed 4000V minimum ESD protection

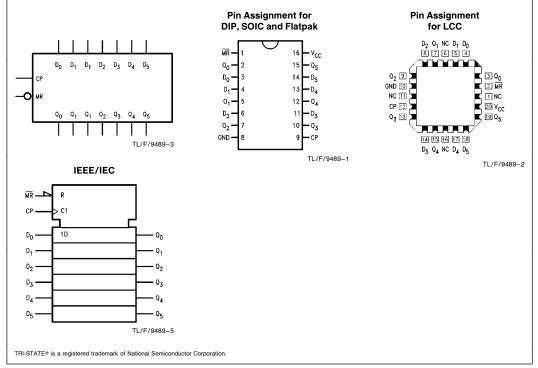
Commercial	Military	Package Number	Package Description		
74F174PC		N16E	16-Lead (0.300" Wide) Molded Dual-In-Line		
	54F174DM (Note 2)	J16A	16-Lead Ceramic Dual-In-Line		
74F174SC (Note 1)		M16A	16-Lead (0.150" Wide) Molded Small Outline, JEDEC		
74F174SJ (Note 1)		M16D	16-Lead (0.300" Wide) Molded Small Outline, EIAJ		
	54F174FM (Note 2)	W16A	16-Lead Cerpack		
	54F174LM (Note 2)	E20A	20-Lead Ceramic Leadless Chip Carrier, Type C		

Note 1: Devices also available in 13" reel. Use Suffix = SCX and SJX.

Note 2: Military grade device with environmental and burn-in processing. Use suffix = DMQB, FMQB and LMQB.

Logic Symbols

Connection Diagrams



91995 National Semiconductor Corporation TL/F/948

RRD-B30M75/Printed in U. S. A.

Unit Loading/Fan Out

		54F/74F			
Pin Names	Description	U.L. HIGH/LOW	Input I _{IH} /I _{IL} Output I _{OH} /I _{OL}		
D ₀ -D ₅ <u>CP</u>	Data Inputs Clock Pulse Input (Active Rising Edge)	1.0/1.0 1.0/1.0	20 μA/ - 0.6 mA 20 μA/ - 0.6 mA		
\overline{MR} Q_0-Q_5	Master Reset Input (Active LOW) Outputs	1.0/1.0 50/33.3	20 μA/ – 0.6 mA – 1 mA/20 mA		

Functional Description

The 'F174 consists of six edge-triggered D flip-flops with individual D inputs and Q outputs. The Clock (CP) and Master Reset ($\overline{\text{MR}}$) are common to all flip-flops. Each D input's state is transferred to the corresponding flip-flop's output following the LOW-to-HIGH Clock (CP) transition. A LOW input to the Master Reset ($\overline{\text{MR}}$) will force all outputs LOW independent of Clock or Data inputs. The 'F174 is useful for capplications where the true output only is required and the Clock and Master Reset are common to all storage elements.

Truth Table

	Inputs	Outputs		
MR	СР	D _n	Q_n	
L	X	Χ	L	
Н	_	Н	Н	
Н	_	L	L	

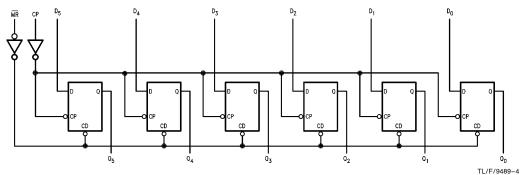
H = HIGH Voltage Level

L = LOW Voltage Level

X = Immaterial

✓ = LOW-to-HIGH Clock Transition

Logic Diagram



Please note that this diagram is provided only for the understanding of logic operations and should not be used to estimate propagation delays.

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

 $\begin{array}{lll} \text{Storage Temperature} & -65^{\circ}\text{C to} + 150^{\circ}\text{C} \\ \text{Ambient Temperature under Bias} & -55^{\circ}\text{C to} + 125^{\circ}\text{C} \\ \text{Junction Temperature under Bias} & -55^{\circ}\text{C to} + 175^{\circ}\text{C} \\ \text{Plastic} & -55^{\circ}\text{C to} + 150^{\circ}\text{C} \\ \end{array}$

V_{CC} Pin Potential to

Voltage Applied to Output in HIGH State (with $V_{CC} = 0V$)

 $\begin{array}{lll} \text{Standard Output} & -0.5 \text{V to V}_{CC} \\ \text{TRI-STATE} \tiny{\$} \text{ Output} & -0.5 \text{V to } +5.5 \text{V} \end{array}$

Current Applied to Output in LOW State (Max) twice the rated I_{OL} (mA)

ESD Last Passing Voltage (Min) 4000V

Note 1: Absolute maximum ratings are values beyond which the device may

Note 1: Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

Recommended Operating Conditions

Free Air Ambient Temperature

Military $-55^{\circ}\text{C to} + 125^{\circ}\text{C}$ Commercial $0^{\circ}\text{C to} + 70^{\circ}\text{C}$

Supply Voltage

Military +4.5V to +5.5V Commercial +4.5V to +5.5V

DC Electrical Characteristics

Symbol	Parameter		54F/74F			Units	V _{CC}	Conditions	
Syllibol			Min	Тур	Max	Oilles	VCC	Conditions	
V _{IH}	Input HIGH Voltage		2.0			V		Recognized as a HIGH Signal	
V_{IL}	Input LOW Voltage				0.8	V		Recognized as a LOW Signal	
V_{CD}	Input Clamp Diode Vo	oltage			-1.2	V	Min	$I_{IN} = -18 \text{ mA}$	
V _{OH}	Output HIGH Voltage	54F 10% V _{CC} 74F 10% V _{CC} 74F 5% V _{CC}	2.5 2.5 2.7			V	Min	$I_{OH} = -1 \text{ mA}$ $I_{OH} = -1 \text{ mA}$ $I_{OH} = -1 \text{ mA}$	
V _{OL}	Output LOW Voltage	54F 10% V _{CC} 74F 10% V _{CC}			0.5 0.5	٧	Min	$I_{OL} = 20 \text{ mA}$ $I_{OL} = 20 \text{ mA}$	
I _{IH}	Input HIGH Current	54F 74F			20.0 5.0	μΑ	Max	$V_{IN} = 2.7V$	
I _{BVI}	Input HIGH Current Breakdown Test	54F 74F			100 7.0	μΑ	Max	V _{IN} = 7.0V	
I _{CEX}	Output HIGH Leakage Current	54F 74F			250 50	μΑ	Max	$V_{OUT} = V_{CC}$	
V_{ID}	Input Leakage Test	74F	4.75			٧	0.0	$I_{\text{ID}} = 1.9 \mu\text{A}$ All Other Pins Grounded	
I _{OD}	Output Leakage Circuit Current	74F			3.75	μΑ	0.0	V _{IOD} = 150 mV All Other Pins Grounded	
I _{IL}	Input LOW Current				-0.6	mA	Max	$V_{IN} = 0.5V$	
I _{OS}	Output Short-Circuit (Current	-60		-150	mA	Max	$V_{OUT} = 0V$	
ICCH	Power Supply Curren	t		30	45	mA	Max	$CP = \sqrt{}$ $D_n = \overline{MR} = HIGH$	
I _{CCL}	Power Supply Curren	t		30	45	mA	Max	$V_O = LOW$	

AC Electrical Characteristics

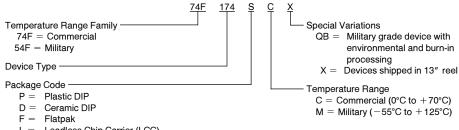
	Parameter	$74F \\ T_A = +25^{\circ}C \\ V_{CC} = +5.0V \\ C_L = 50 pF$			54F T _A , V _{CC} = Mil C _L = 50 pF		74F T _A , V _{CC} = Com C _L = 50 pF		Units
Symbol									
		Min	Тур	Max	Min	Max	Min	Max	
f _{max}	Maximum Clock Frequency	80			70		80		MHz
t _{PLH}	Propagation Delay CP to Q _n	3.5 4.0	5.5 7.0	8.0 10.0	3.0 4.0	10.0 12.0	3.5 4.0	9.0 11.0	ns
t _{PHL}	Propagation Delay MR to Q _n	5.0	10.0	14.0	5.0	16.0	5.0	15.0	ns

AC Operating Requirements

		$74F$ $T_A = +25^{\circ}C$ $V_{CC} = +5.0V$		54	F	74F		
Symbol	Parameter			$\mathbf{T_A,V_{CC}} = \mathbf{Mil}$		T _A , V _{CC} = Com		Units
		Min	Max	Min	Max	Min	Max	
t _s (H) t _s (L)	Setup Time, HIGH or LOW D _n to CP	4.8 4.0		5.0 5.0		4.8 4.0		- ns
t _h (H)	Hold Time, HIGH or LOW D _n to CP	0 0		2.0 2.0		0		113
t _w (H)	CP Pulse Width HIGH or LOW	4.0 6.0		5.0 7.5		4.0 6.0		ns
t _w (L)	MR Pulse Width, LOW	5.0		6.5		5.0		ns
t _{rec}	Recovery Time, MR to CP	5.0		6.0		5.0		



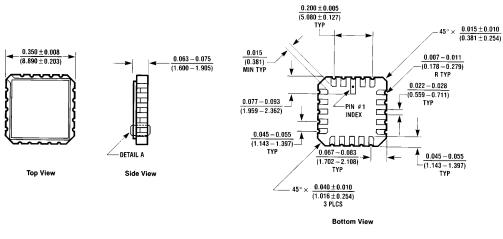
The device number is used to form part of a simplified purchasing code where the package type and temperature range are defined as follows:

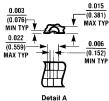


L = Leadless Chip Carrier (LCC) S = Small Outline SOIC JEDEC

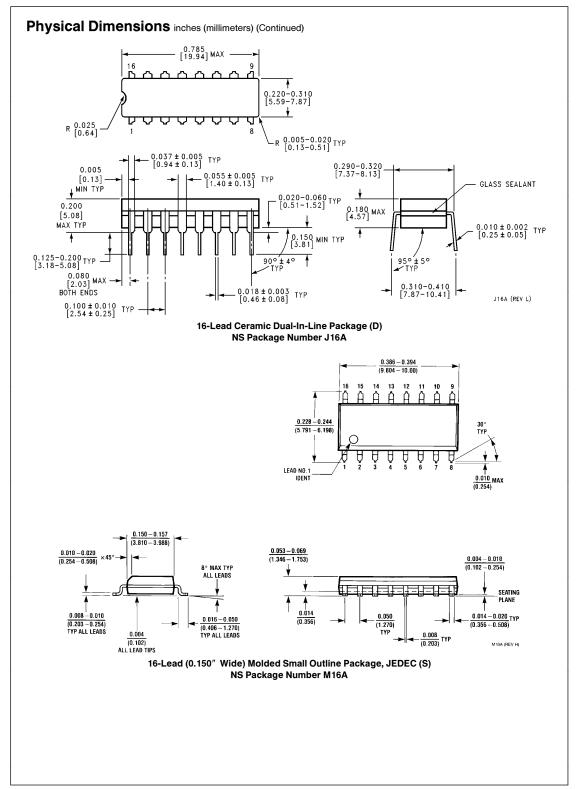
SS = Small Outline SOIC EIAJ

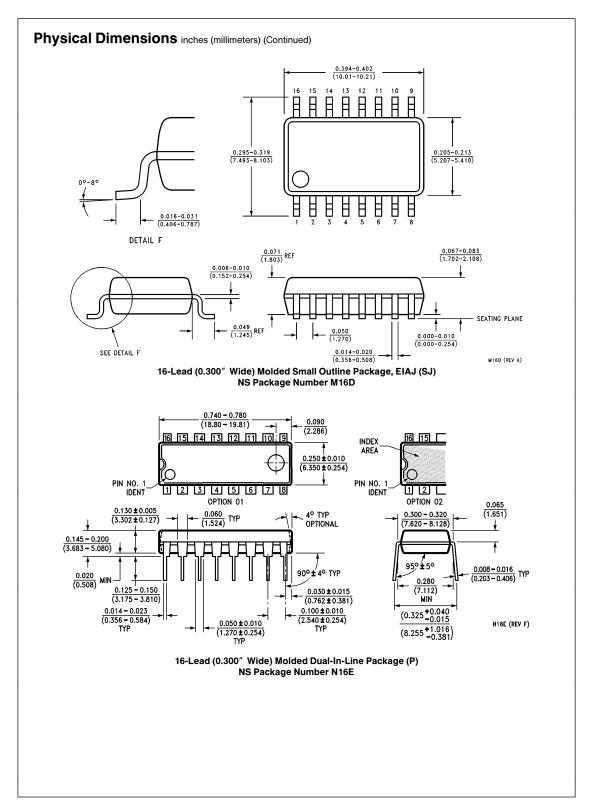
Physical Dimensions inches (millimeters)



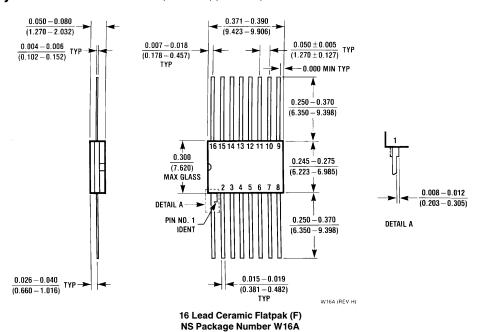


20-Terminal Ceramic Leadless Chip Carrier (L) NS Package Number E20A E20A (REV D)





Physical Dimensions inches (millimeters) (Continued)



LIFE SUPPORT POLICY

NATIONAL'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT OF NATIONAL SEMICONDUCTOR CORPORATION. As used herein:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform, when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
- A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.



National Semiconductor Corporation 2900 Semiconductor Drive P.O. Box 58090 Santa Clara, CA 95052-8090 Tel: 1(800) 272-9959 TWX: (910) 339-9240 National Semiconductor GmbH Livry-Gargan-Str. 10 D-82256 Fürstenfeldbruck Germany Tel: (81-41) 35-0 Telex: 527649 Fax: (81-41) 35-1 National Semiconductor Japan Ltd. Sumitomo Chemical Engineering Center Bldg. 7F 1-7-1, Nakase, Mihama-Ku Chiba-City, Ciba Prefecture 261

National Semiconductor Hong Kong Ltd. 13th Floor, Straight Block, Ocean Centre, 5 Canton Rd. Tsimshatsui, Kowloon U Hong Kong Tel: (852) 2737-1600 Fax: (852) 2736-9960 National Semiconductores Do Brazil Ltda. Rue Deputado Lacorda Franco 120-3A Sao Paulo-SP Brazil 05418-000 Tel: (55-11) 212-5066 Telex: 391-1131931 NSBR BR Fax: (55-11) 212-1181 National Semiconductor (Australia) Pty, Ltd. Building 16 Business Park Drive Monash Business Park Nottinghill, Melbourne Victoria 3168 Australia Tel: (3) 558-9999 Fax: (3) 558-9998

National does not assume any responsibility for use of any circuitry described, no circuit patent licenses are implied and National reserves the right at any time without notice to change said circuitry and specifications.